

**Amendments to the Claims**

1. (*Currently Amended*) A structure for a semiconductor arrangement; comprising a resist structure coupled to a substrate; the resist structure comprising:
  - [[-]]a depression (301) for depositing of a solution containing a semiconductor or a precursor thereof (309) and
  - [[-]]a trough (305) aligning at least part of an edge of the depression (309) and separated from the depression (301) by a protrusion (307).
2. (*Original*) A structure as claimed in claim 1 wherein the resist structure is formed in a single layer of the semiconductor arrangement.
3. (*Currently Amended*) A structure as claimed in claim 1 wherein the trough (305) substantially surrounds the depression (301).
4. (*Currently Amended*) A structure as claimed in claim 1 wherein the semiconductor (309) is an organic semiconductor.
5. (*Currently Amended*) A structure as claimed in claim 1 wherein a width of an end of the protrusion (307) distal from the substrate is larger than a width of an end of the protrusion (307) proximal to the substrate.
6. (*Currently Amended*) A structure as claimed in claim 1 wherein a width of an end of the protrusion (307) proximal to the substrate is larger than a width of an end of the protrusion (307) distal from the substrate.
7. (*Currently Amended*) A structure ~~as claimed in claim 5 or 6 as claimed in claim 5,~~ wherein the protrusion (307) has a substantially frusto-conical cross section.
8. (*Original*) A structure as claimed in claim 1 wherein the resist structure is formed by a polymer layer.

9. (*Currently Amended*) A structure as claimed in claim 1 wherein a cross section of the depression (301) substantially perpendicular to the direction of depression comprises rounded corners.
10. (*Currently Amended*) A structure as claimed in claim 1 wherein a cross section of the depression (301) substantially perpendicular to the direction of depression is substantially rectangular.
11. (*Currently Amended*) A structure as claimed in claim 1 wherein a depth of the trough (305) is substantially the same as a depth of the depression (301).
12. (*Currently Amended*) A structure as claimed in claim 1 wherein the depression (301) comprises a semiconductor forming an active layer of a field effect transistor.
13. (*Currently Amended*) A structure as claimed in claim 12 wherein the field effect transistor comprises a source (601) and drain (603) having a plurality of interdigitated electrodes and a gate (605) extending across the plurality of interdigitated electrodes.
14. (*Currently Amended*) A structure as claimed in claim 13 wherein the depression (301) extends beyond the gate (605) in a direction substantially perpendicular to the longitudinal direction of the interdigitated fingers.
15. (*Currently Amended*) A structure as claimed in claim 14 wherein the depression (301) does not extend beyond the gate (605) in a direction substantially aligned with the longitudinal direction of the interdigitated fingers.
16. (*Currently Amended*) An electronic device comprising the resist structure of ~~any of the claims 1-15. of claim 1.~~

17. (*Currently Amended*) ~~An electronic device as claimed in claim 16 provided with an integrated circuit comprising the structure of claim 12.~~

An electronic device, comprising a resist structure coupled to a substrate; the resist structure comprising:

a depression for depositing of a solution containing a semiconductor or a precursor thereof and

a trough aligning at least part of an edge of the depression and separated from the depression by a protrusion,

wherein the depression comprises a semiconductor forming an active layer of a field effect transistor.

18. (*Currently Amended*) ~~An electronic device as claimed in claim 16, provided with an active matrix backplane or active matrix display comprising the structure of claim 12.~~

An electronic device comprising a resist structure coupled to a substrate; the resist structure comprising:

a depression for depositing of a solution containing a semiconductor or a precursor thereof and

a trough aligning at least part of an edge of the depression and separated from the depression by a protrusion, provided with

an active matrix backplane or active matrix display comprising,

a structure for a semiconductor arrangement; comprising a resist structure coupled to a substrate; the resist structure comprising:

a depression for depositing of a solution containing a semiconductor or a precursor thereof and

a trough aligning at least part of an edge of the depression and separated from the depression by a protrusion,

wherein the depression comprises a semiconductor forming an active layer of a field effect transistor.

19. (*Original*) An electroluminescent device comprising the structure of claim 12.

20. (*Currently Amended*) A method of manufacturing a semiconductor arrangement; the method comprising the steps of:

[[ - ]]] providing a substrate;

[[ - ]]] applying a resist structure coupled to the substrate; the resist structure comprising a depression (301) for depositing of a solution containing a semiconductor (309) or a precursor thereof and a trough aligning at least part of an edge of the depression (301) and separated from the depression (301) by a protrusion (307); and

[[ - ]]] depositing the solution containing the semiconductor (309) in the depression (301).

21. (*Currently Amended*) A method as claimed in claim 20 wherein the depositing of the solution (309) is by a printing process.

22. (*Currently Amended*) A method as claimed in claim 21 wherein the depositing of the solution (309) is by an ink jet printing process.